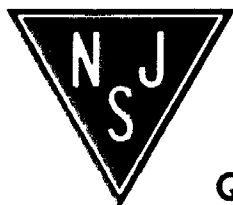


TYPES 2N1303, 2N1305, 2N1307, AND 2N1309 P-N-P ALLOY-JUNCTION GERMANIUM TRANSISTORS

electrical characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS	2N1303			2N1305			2N1307			2N1309			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
BV_{CBO} Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-30	—	—	-30	—	—	-30	—	—	-30	—	—	v
BV_{EBO} Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-25	—	—	-25	—	—	-25	—	—	-25	—	—	v
V_{PT} Punch Through Voltage†	$V_{EBI} = -1 v$	-25	—	—	-20	—	—	-15	—	—	-15	—	—	v
I_{CBO} Collector Cutoff Current	$V_{CB} = -25 v, I_E = 0$	—	-2	-6	—	-2	-6	—	-2	-6	—	-2	-6	μA
I_{EBO} Emitter Cutoff Current	$V_{EB} = -25 v, I_C = 0$	—	-1.5	-6	—	-1.5	-6	—	-1.5	-6	—	-1.5	-6	μA
h_{FE} Static Forward Current Transfer Ratio	$V_{CE} = -1 v, I_C = -10 ma$	20	100	—	40	115	200	40	130	300	80	160	—	—
	$V_{CE} = -0.35 v, I_C = -200 ma$	10	45	—	15	55	—	20	65	—	20	75	—	—
V_{BE} Base-Emitter Voltage	$I_B = -0.5 ma, I_C = -10 ma$	-0.15	-0.25	-0.40	-0.15	-0.25	-0.35	-0.15	-0.25	-0.35	-0.15	-0.25	-0.35	v
$V_{CE(sat)}$ Collector-Emitter Saturation Voltage	$I_B = -0.5 ma, I_C = -10 ma$	—	-0.08	-0.20	—	—	—	—	—	—	—	—	—	v
	$I_B = -0.25 ma, I_C = -10 ma$	—	—	—	—	-0.08	-0.20	—	—	—	—	—	—	v
	$I_B = -0.17 ma, I_C = -10 ma$	—	—	—	—	—	—	—	-0.08	-0.20	—	—	—	v
	$I_B = -0.13 ma, I_C = -10 ma$	—	—	—	—	—	—	—	—	—	—	-0.08	-0.20	v
h_{ib} Small-Signal Common-Base Input Impedance	$V_{CB} = -5 v, I_E = 1 ma, f = 1 kc$	—	29	—	—	29	—	—	29	—	—	29	—	ohm
h_{rb} Small-Signal Common-Base Reverse Voltage Transfer Ratio	$V_{CB} = -5 v, I_E = 1 ma, f = 1 kc$	—	7×10^{-4}	—	—	7×10^{-4}	—	—	7×10^{-4}	—	—	7×10^{-4}	—	—
h_{ob} Small-Signal Common-Base Output Admittance	$V_{CB} = -5 v, I_E = 1 ma, f = 1 kc$	—	0.40	—	—	0.40	—	—	0.40	—	—	0.40	—	μmho
h_{ie} Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = -5 v, I_C = -1 ma, f = 1 kc$	—	115	—	—	130	—	—	150	—	—	190	—	—
α_{hfb} Common-Base Alpha—Cutoff Frequency	$V_{CB} = -5 v, I_E = 1 ma$	3	12	—	5	14	—	10	16	—	15	20	—	mc
C_{ob} Common-Base Open-Circuit Output Capacitance	$V_{CB} = -5 v, I_E = 0, f = 1 mc$	—	10	20	—	10	20	—	10	20	—	10	20	pf
C_{ib} Common-Base Open-Circuit Input Capacitance	$V_{EB} = -5 v, I_C = 0, f = 1 mc$	—	9	—	—	9	—	—	9	—	—	9	—	pf

† V_{PT} is determined by measuring the emitter-base floating potential V_{EBI} . The collector-base voltage, V_{CB} , is increased until $V_{EBI} = -1$ volt; this value of $V_{CB} = (V_{PT} - 1 v)$.



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Quality Semi-Conductors

switching characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS††	2N1303			2N1305			2N1307			2N1309			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
τ_d Delay Time	$I_C = -10 \text{ ma}$, $I_{B(1)} = -1.3 \text{ ma}$ $I_{B(2)} = 0.7 \text{ ma}$, $V_{BE(off)} = 0.8 \text{ v}$ $R_L = 1 \text{ k } \Omega$ (See Fig. 1)	—	0.06	—	—	0.06	—	—	0.06	—	—	0.05	—	μsec
τ_r Rise Time		—	0.18	—	—	0.18	—	—	0.14	—	—	0.14	—	μsec
τ_s Storage Time		—	0.80	—	—	0.80	—	—	0.78	—	—	0.76	—	μsec
τ_f Fall Time		—	0.38	—	—	0.38	—	—	0.36	—	—	0.30	—	μsec
Q_{sb} Stored Base Charge	$I_{B(1)} = -1 \text{ ma}$, $I_C = -10 \text{ ma}$ (See Fig. 2)	—	960	—	—	920	—	—	880	—	—	800	—	pc

††Voltage and current values shown are nominal, exact values vary slightly with device parameters.

operating characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS	2N1303			2N1305			2N1307			2N1309			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
HF Spot Noise Figure	$V_{CB} = -5 \text{ v}$ $I_B = 1 \text{ ma}$ $I = 1 \text{ kc}$, $R_E = 1 \text{ k } \Omega$	—	4	—	—	4	—	—	3	—	—	3	—	dB